

Gate resistor installed Dual N-channel MOSFET

KFCAB21350L Data Sheet

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1. GENERAL DESCRIPTION

Gate resistor installed Dual N-channel MOSFET

For lithium-ion secondary battery protection circuits

2. FEATURES

- Source-source On-state resistance: $R_{SS} (on) \text{ typ.} = 2.1 \text{ m}\Omega$ ($V_{GS} = 4.5 \text{ V}$)
- CSP (Chip Size Package)
- RoHS compliant (EU RoHS / MSL: Level 1 compliant)

3. MARKING SYMBOL: 3M

4. PACKAGING

Embossed type (Thermo-compression sealing): 10,000 pcs / reel (standard)

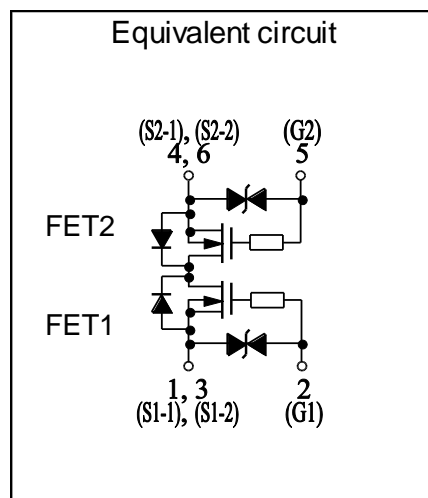
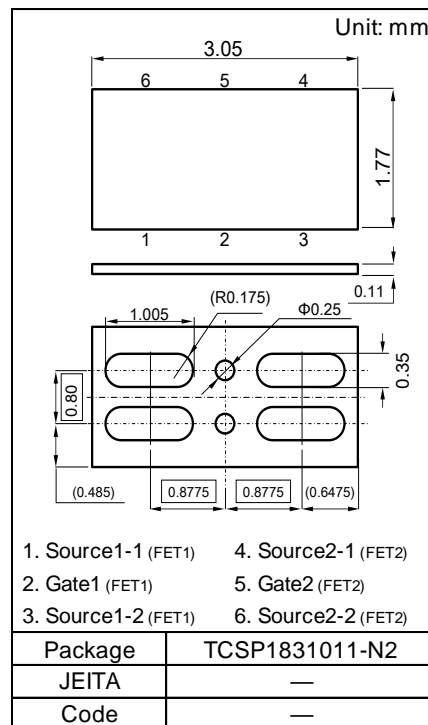
5. ABSOLUTE MAXIMUM RATINGS $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Source-source Voltage		VSS	12	V
Gate-source Voltage		VGS	± 8	V
Source Current	DC ^{*1}	IS1	12	A
	DC ^{*2}	IS2	27	
	Pulsed ^{*3}	ISp	120	
Total Power Dissipation	DC ^{*1}	PD1	0.45	W
	DC ^{*2}	PD2	2.1	
Channel Temperature		Tch	150	$^\circ\text{C}$
Storage Temperature Range		Tstg	-55 to +150	$^\circ\text{C}$

6. THERMAL CHARACTERISTICS $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Thermal Resistance (ch-a)	Rth1 ^{*1}	278	$^\circ\text{C} / \text{W}$
	Rth2 ^{*2}	59	

- Note
- *1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm) using the minimum recommended pad size (36 μm Copper).
 - *2 Mounted on Ceramic substrate (70 mm x 70 mm x t1.0 mm).
 - *3 $t = 10 \mu\text{s}$, Duty Cycle $\leq 1 \%$



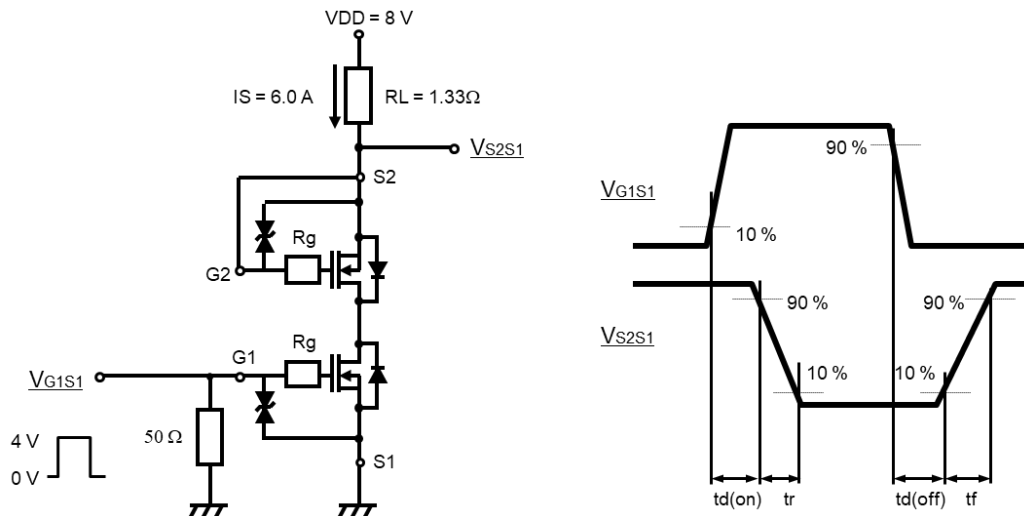
7. ELECTRICAL CHARACTERISTICS $T_a = 25\text{ }^{\circ}\text{C} \pm 3\text{ }^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Source-source Breakdown Voltage	VSSS	$I_S = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	12			V
Zero Gate Voltage Source Current	ISSS	$V_{SS} = 12\text{ V}$, $V_{GS} = 0\text{ V}$			1.0	μA
Gate-source Leakage Current	IGSS1	$V_{GS} = \pm 8\text{ V}$, $V_{SS} = 0\text{ V}$			± 10	μA
	IGSS2	$V_{GS} = \pm 5\text{ V}$, $V_{SS} = 0\text{ V}$			± 1.0	
Gate-source Threshold Voltage	V _{th}	$I_S = 1.41\text{ mA}$, $V_{SS} = 10\text{ V}$	0.35	0.90	1.40	V
Source-source On-state Resistance	RSS(on)1	$I_S = 6.0\text{ A}$, $V_{GS} = 4.5\text{ V}$	1.55	2.10	2.75	$\text{m}\Omega$
	RSS(on)2	$I_S = 6.0\text{ A}$, $V_{GS} = 3.8\text{ V}$	1.60	2.20	2.85	
	RSS(on)3	$I_S = 6.0\text{ A}$, $V_{GS} = 3.1\text{ V}$	1.65	2.40	3.95	
	RSS(on)4	$I_S = 6.0\text{ A}$, $V_{GS} = 2.5\text{ V}$	1.90	3.10	6.10	
Body Diode Forward Voltage	V _{F(s-s)}	$I_F = 6.0\text{ A}$, $V_{GS} = 0\text{ V}$		0.8	1.2	V
Input Capacitance *1	Ciss	$V_{SS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ kHz}$		4650		pF
Output Capacitance *1	Coss			580		
Reverse Transfer Capacitance *1	Crss			530		
Turn-on Delay Time *1,*2	t _{d(on)}	$V_{DD} = 8\text{ V}$, $V_{GS} = 0\text{ to }4\text{ V}$ $I_S = 6.0\text{ A}$		1.2		μs
Rise Time *1,*2	t _r			2.3		
Turn-off Delay Time *1,*2	t _{d(off)}	$V_{DD} = 8\text{ V}$, $V_{GS} = 4\text{ to }0\text{ V}$ $I_S = 6.0\text{ A}$		9.0		μs
Fall Time *1,*2	t _f			5.0		
Total Gate Charge *1	Q _g	$V_{DD} = 8\text{ V}$ $V_{GS} = 0\text{ to }4\text{ V}$ $I_S = 6.0\text{ A}$		43		nC
Gate-source Charge *1	Q _{gs}			10		
Gate-drain Charge *1	Q _{gd}			10		

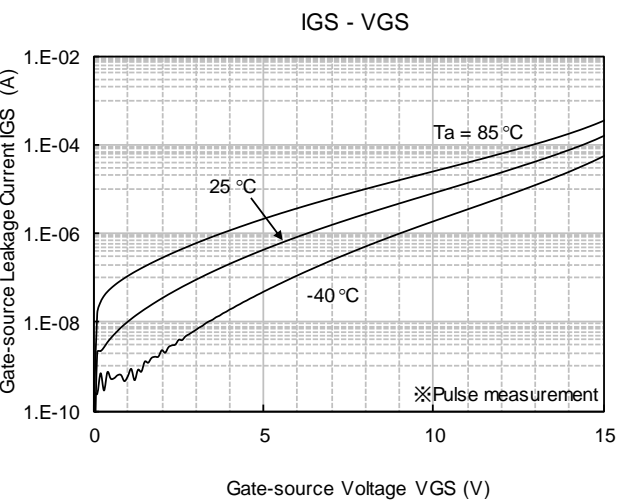
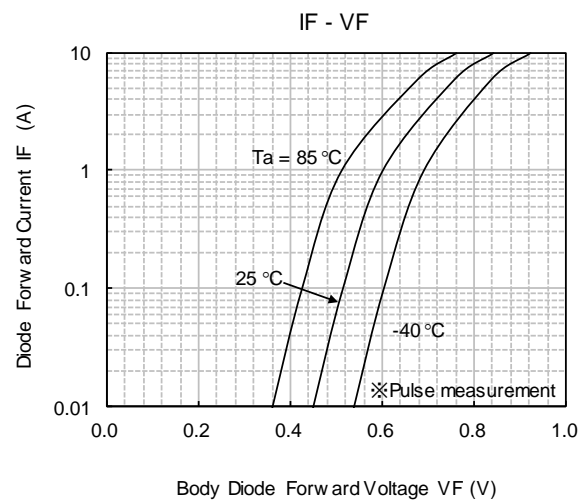
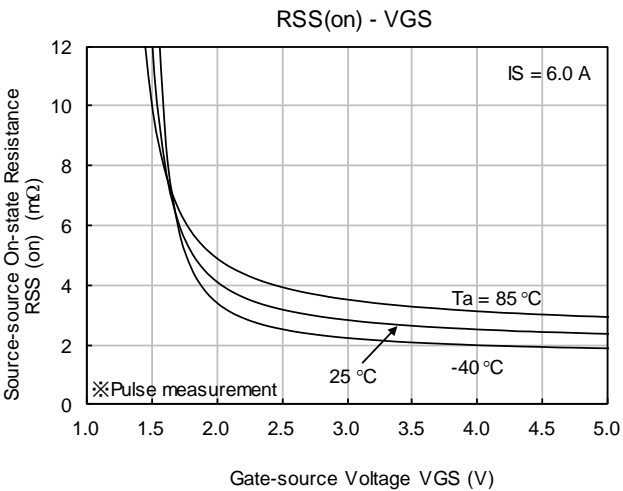
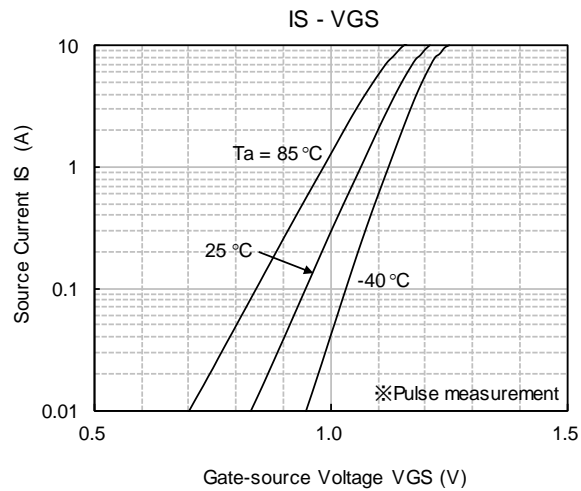
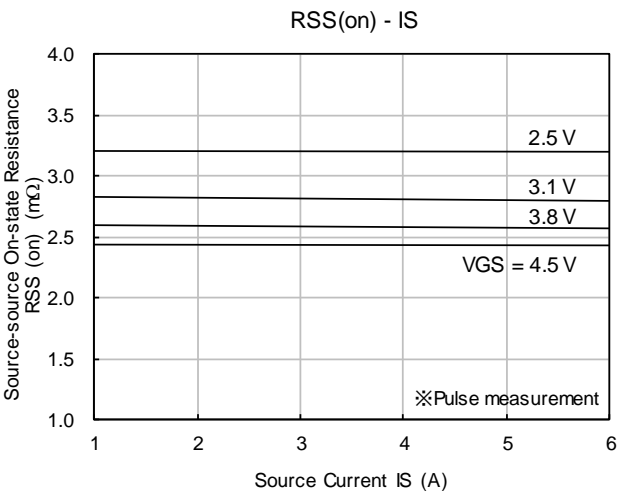
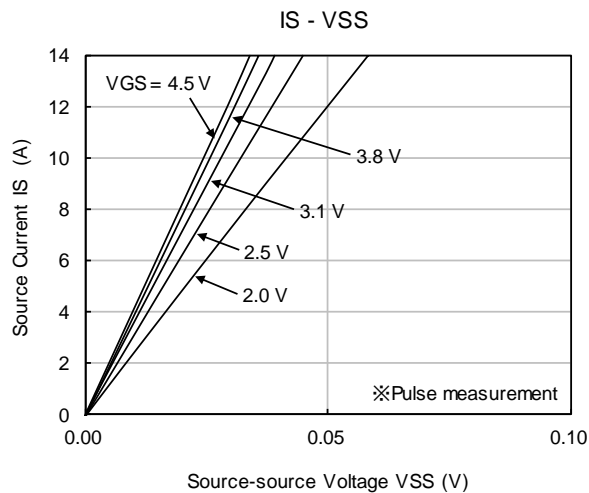
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

*1 Guaranteed by design, not subject to production testing

*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

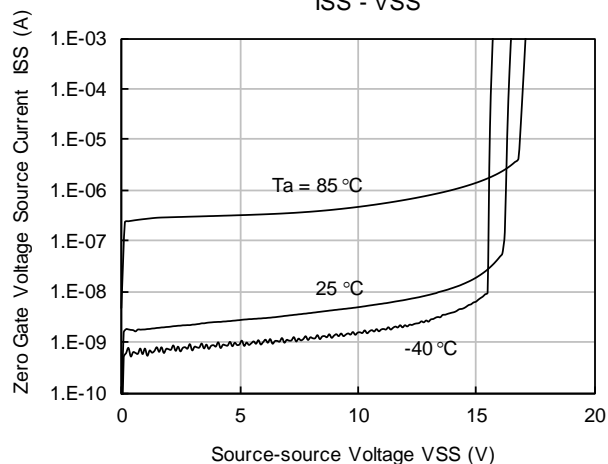


8. TECHNICAL DATA (Reference)

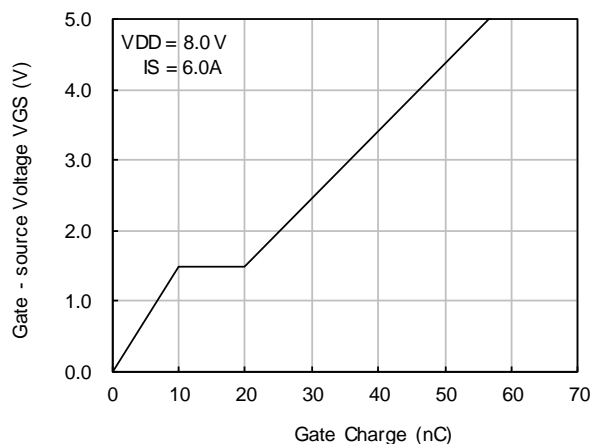


TECHNICAL DATA (Reference)

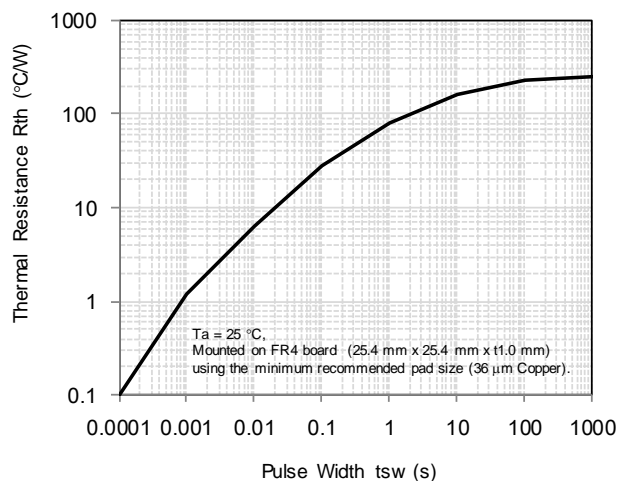
ISS - VSS



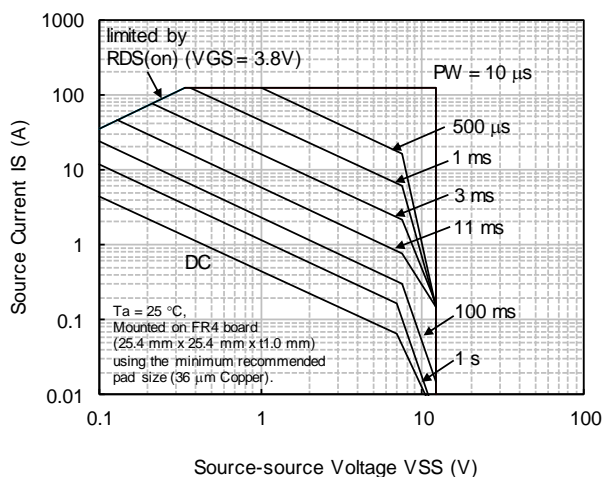
Dynamic Input / Output Characteristics



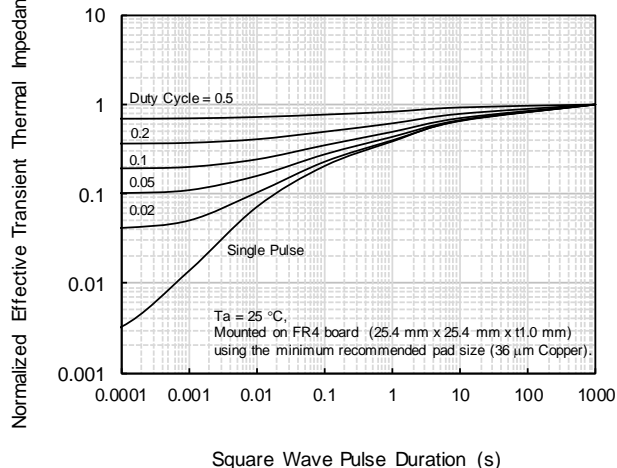
Rth - tsw



Safe Operating Area

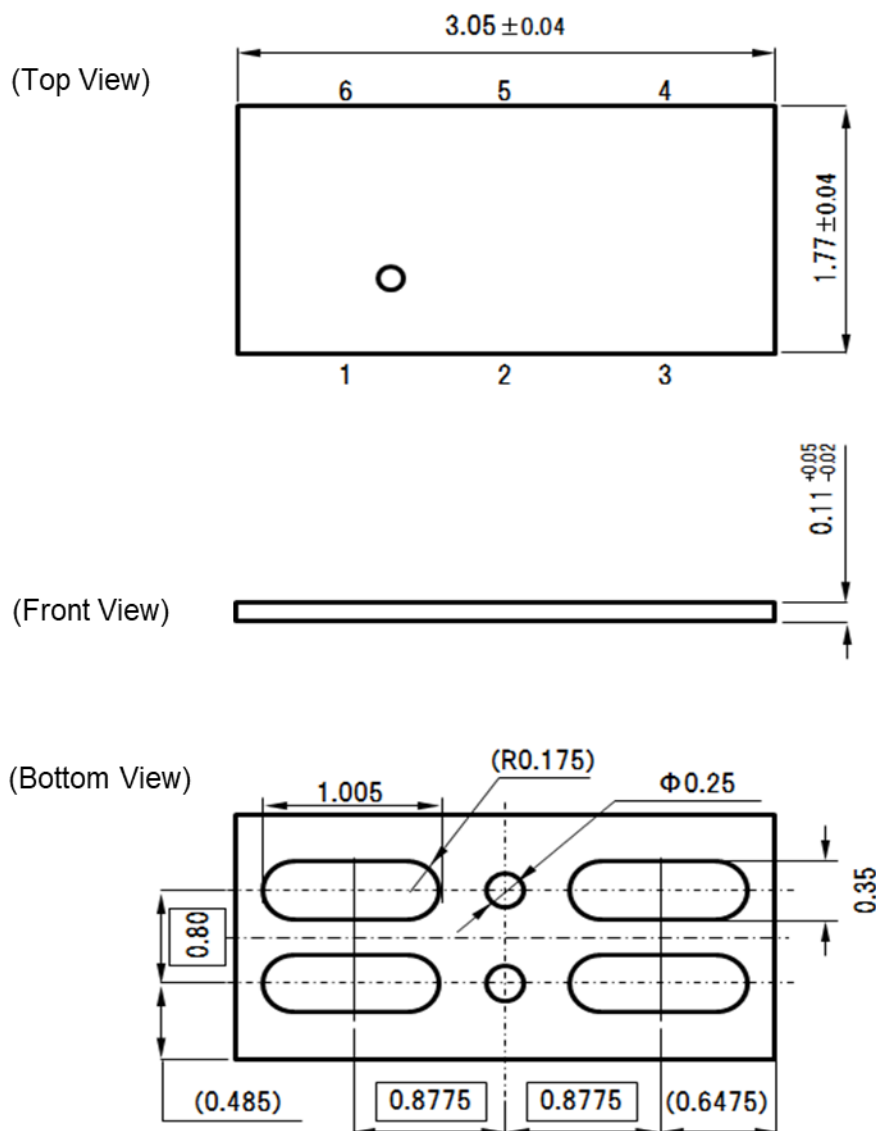


Thermal Response



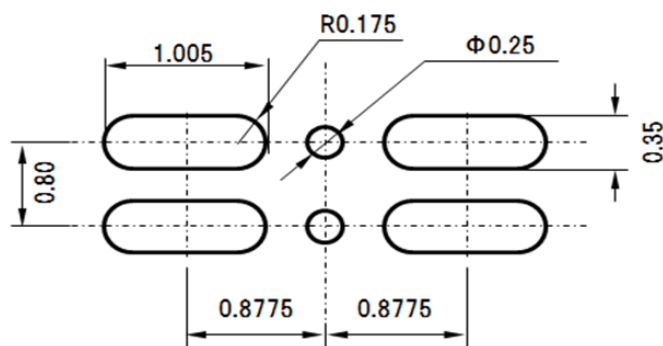
9. OUTLINE

Unit : mm



10. LAND PATTERN (Reference)

Unit : mm



11. REVISION HISTORY

Date	Revision	Description
2021.2.8	1.00	1. initially issued.

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